

IN THE CLAIMS:

Please amend the following claims 46-88 as follows.

1-45. (Canceled)

46. (previously presented) A semiconductor device comprising:

a first thin film transistor formed over an insulating surface, the first thin film transistor comprising:

a semiconductor film comprising crystalline silicon and having at least source and drain regions and a channel forming region;

a gate insulating film over the channel forming region; and

a gate electrode formed over the gate insulating film; an interlayer insulating film formed over the first thin film transistor;

a conductive layer formed over the interlayer insulating film and electrically connected to one of the source and drain regions of the first thin film transistor;

a color filter having a flattened surface formed over the interlayer insulating film and the conductive layer; and

a pixel electrode formed over the color filter and electrically connected to the conductive layer.

47. (previously presented) A semiconductor device comprising:

a first thin film transistor formed over an insulating surface, the first thin film transistor comprising:

a semiconductor film comprising at least a channel forming region;

a gate insulating film adjacent to the channel forming region; and

a gate electrode adjacent to the gate insulating film, an interlayer insulating film formed over the first thin film transistor;

a conductive layer formed over the interlayer insulating film and electrically connected to one of source and drain regions of the first thin film transistor;

a color filter having a flattened surface formed over the interlayer insulating film and the conductive layer; and

a pixel electrode formed over the color filter and electrically connected to the conductive layer.

48. (previously presented) A semiconductor device comprising:

a first thin film transistor formed over an insulating surface, the first thin film transistor comprising:

a semiconductor film comprising crystalline silicon and having at least source and drain regions and a channel forming region;

a gate insulating film adjacent to the channel forming region; and

a gate electrode adjacent to the channel forming region with the gate insulating film interposed therebetween;

an interlayer insulating film formed over the first thin film transistor, the interlayer insulating film comprising at

least a material selected from the group consisting of silicon nitride, silicon oxide and nitrated silicon oxide;

a color filter having a flattened surface formed over the interlayer insulating film; and

a pixel electrode formed over the color filter,

wherein the pixel electrode is electrically connected to the first thin film transistor.

49. (previously presented) A device according to claim 48, wherein the gate electrode is located over the channel forming region.

50. (previously presented) A semiconductor device comprising:

a first thin film transistor formed over an insulating surface, the first thin film transistor comprising:

a semiconductor film comprising silicon and having at least a channel forming region;

a gate insulating film adjacent to the channel forming region; and

a gate electrode adjacent to the channel forming region with the gate insulating film interposed therebetween;

an interlayer insulating film formed over the first thin film transistor, the interlayer insulating film comprising at least a material selected from the group consisting of silicon nitride, silicon oxide and nitrated silicon oxide;

a color filter having a flattened surface formed over the interlayer insulating film; and

a pixel electrode formed over the color filter.

51. (previously presented) A device according to claim 50, wherein the gate electrode is located over the channel forming region.

52. (previously presented) A semiconductor device comprising:

a first thin film transistor formed over an insulating surface, the first thin film transistor comprising:

a semiconductor film comprising crystalline silicon and having at least source and drain regions and a channel forming region;

a gate insulating film adjacent to the channel forming region; and

a gate electrode formed adjacent to the channel forming region with the gate insulating film interposed therebetween;

a first interlayer insulating film formed over the first thin film transistor;

a conductive layer formed over the first interlayer insulating film and electrically connected to one of the source and drain regions of the first thin film transistor;

a passivation film formed over the conductive layer, the passivation film comprising at least a material selected from the group consisting of silicon nitride, silicon oxide and nitrated silicon oxide;

a color filter having a flattened surface formed over the passivation film; and

a pixel electrode formed over the color filter and electrically connected to the conductive layer.

53. (previously presented) A device according to claim 52, wherein the gate electrode is located over the channel forming region.

54. (previously presented) A semiconductor device comprising:

a first thin film transistor formed over a substrate, the first thin film transistor comprising:

a semiconductor film comprising silicon and having at least a channel forming region;

a gate insulating film adjacent to the channel forming region; and

a gate electrode adjacent to the channel forming region with the gate insulating film interposed therebetween;

a first interlayer insulating film formed over the first thin film transistor;

a conductive layer formed over the first interlayer insulating film and electrically connected to one of the source and drain regions of the first thin film transistor;

a passivation film formed over the conductive layer, the passivation film comprising at least a material selected from the group consisting of silicon nitride and nitrated silicon oxide;

a color filter having a flattened surface formed over the passivation film; and

a pixel electrode formed over the color filter and electrically connected to the conductive layer.

55. (previously presented) A device according to claim 54, wherein the gate electrode is located over the channel forming region.

56. (previously presented) A semiconductor device comprising:

a first thin film transistor formed over an insulating surface, the first thin film transistor comprising:

a semiconductor film comprising :

a channel forming region; and

a source region and a drain region in contact with the LDD regions;

a gate insulating film adjacent to the channel forming region; and

a gate electrode adjacent to the gate insulating film;

an interlayer insulating film formed over the first thin film transistor;

a conductive layer formed over the interlayer insulating film and electrically connected to one of source and drain regions of the first thin film transistor;

a color filter formed over the interlayer insulating film, the conductive layer and the first thin film transistor; and

a pixel electrode formed over the color filter and electrically connected to the conductive layer.

57. (previously presented) A semiconductor device comprising:

a first thin film transistor formed over an insulating surface, the first thin film transistor comprising:

a semiconductor film comprising:

a channel forming region; and

a source region and a drain region in contact with the LDD regions;

a gate insulating film adjacent to the channel forming region; and

a gate electrode adjacent to the channel forming region with the gate insulating film interposed therebetween;

an interlayer insulating film formed over the first thin film transistor, the interlayer insulating film comprising at least a material selected from the group consisting of silicon nitride, silicon oxide and nitrated silicon oxide;

a color filter formed over the interlayer insulating film and the first thin film transistor; and

a pixel electrode formed over the color filter.

58. (previously presented) A semiconductor device comprising:

a first thin film transistor formed over an insulating surface, the first thin film transistor comprising:

a semiconductor film comprising:

a channel forming region; and

a source region and a drain region in contact with the LDD regions;

a gate insulating film adjacent to the channel forming region; and

a gate electrode adjacent to the channel forming region with the gate insulating film interposed therebetween;

a first interlayer insulating film formed over the first thin film transistor;

a conductive layer formed over the first interlayer insulating film and electrically connected to one of the source and drain regions of the first thin film transistor;

a passivation film formed over the conductive layer, the passivation film comprising at least a material selected from the group consisting of silicon nitride and nitrated silicon oxide;

a color filter formed over the passivation film and the first thin film transistor; and

a pixel electrode formed over the color filter and electrically connected to the conductive layer.

59. (previously presented) A semiconductor device comprising:

a first thin film transistor comprising:

a semiconductor film comprising at least a channel forming region;

a gate insulating film adjacent to the channel forming region; and

a gate electrode adjacent to the channel forming region with the gate insulating film interposed therebetween;

an interlayer insulating film formed over the first thin film transistor;



a conductive layer formed over the interlayer insulating film and electrically connected to one of source and drain regions of the first thin film transistor;

a color filter formed over the interlayer insulating film, the conductive layer and the first thin film transistor; and

a pixel electrode formed over the color filter and electrically connected to the conductive layer;

~~wherein the pixel matrix circuit and the driver circuit are over a same substrate.~~

60. (previously presented) A semiconductor device comprising:

a first thin film transistor comprising:

a semiconductor film comprising silicon and having at least a channel forming region;

a gate insulating film adjacent to the channel forming region; and

a gate electrode adjacent to the channel forming region with the gate insulating film interposed therebetween;

an interlayer insulating film formed over the first thin film transistor, the interlayer insulating film comprising at least a material selected from the group consisting of silicon nitride, silicon oxide and nitrated silicon oxide;

a color filter formed over the interlayer insulating film and the first thin film transistor; and

a pixel electrode formed over the color filter.

61. (previously presented) A semiconductor device comprising:

a first thin film transistor comprising:

a semiconductor film comprising silicon and having at least a channel forming region;

a gate insulating film adjacent to the channel forming region; and

a gate electrode adjacent to the channel forming region with the gate insulating film interposed therebetween;

a first interlayer insulating film formed over the first thin film transistor;

a conductive layer formed over the first interlayer insulating film and electrically connected to one of the source and drain regions of the first thin film transistor;

a passivation film formed over the conductive layer, the passivation film comprising at least a material selected from the group consisting of silicon nitride and nitrated silicon oxide;

a color filter formed over the passivation film and the first thin film transistor; and

a pixel electrode formed over the color filter and electrically connected to the conductive layer.

62. (previously presented) A device according to claim 56, wherein the semiconductor film comprises crystalline silicon.

63. (previously presented) A device according to claim 57, wherein the semiconductor film comprises crystalline silicon.

64. (previously presented) A device according to claim 58, wherein the semiconductor film comprises crystalline silicon.

65. (previously presented) A device according to claim 59, wherein the semiconductor film comprises crystalline silicon.

66. (previously presented) A device according to claim 60, wherein the semiconductor film comprises crystalline silicon.

67. (previously presented) A device according to claim 61, wherein the semiconductor film comprises crystalline silicon.

68. (Currently Amended) A device according to claim 46, wherein the semiconductor device further comprising:

a resin film over the color filter;

an electrode over the organic resin film; and

an oxide film of the ~~first~~ electrode in direct contact with at least a portion of a surface of the ~~first~~ electrode,

wherein the pixel electrode is in direct contact with at least a portion of the oxide film, and

wherein a storage capacitor comprises the electrode and the pixel electrode with the oxide film interposed therebetween.

69. (Currently Amended) A device according to claim 48, wherein the semiconductor device further comprising:

a resin film over the color filter;

an electrode over the organic resin film; and

an oxide film of the ~~first~~ electrode in direct contact with at least a portion of a surface of the ~~first~~ electrode,

wherein the pixel electrode is in direct contact with at least a portion of the oxide film, and

wherein a storage capacitor comprises the ~~first~~ electrode and the pixel electrode with the oxide film interposed therebetween.

70. (Currently Amended) A device according to claim 52, wherein the semiconductor device further comprising:

a resin film over the color filter;

an electrode over the organic resin film; and

an oxide film of the ~~first~~ electrode in direct contact with at least a portion of a surface of the ~~first~~ electrode,

wherein the pixel electrode is in direct contact with at least a portion of the oxide film, and

wherein a storage capacitor comprises the ~~first~~ electrode and the pixel electrode with the oxide film interposed therebetween.

71. (previously presented) A device according to claim 46, wherein the semiconductor film further comprises LDD regions between the channel forming region and the source and drain regions.

72. (previously presented) A device according to claim 48, wherein the semiconductor film further comprises LDD regions

between the channel forming region and the source and drain regions.

73. (previously presented) A device according to claim 52, wherein the semiconductor film further comprises LDD regions between the channel forming region and the source and drain regions.

74. (previously presented) A device according to claim 56, wherein the semiconductor film further comprises LDD regions between the channel forming region and the source and drain regions.

75. (previously presented) A device according to claim 57, wherein the semiconductor film further comprises LDD regions between the channel forming region and the source and drain regions.

76. (previously presented) A device according to claim 58, wherein the semiconductor film further comprises LDD regions between the channel forming region and the source and drain regions.

77. (previously presented) A device according to claim 46, further comprising a driver circuit comprising a second thin film transistor,

wherein the first thin film transistor is included in a pixel matrix circuit, and

wherein the pixel matrix circuit and the driver circuit are formed over an insulating surface.

78. (previously presented) A device according to claim 47, further comprising a driver circuit comprising a second thin film transistor,

wherein the first thin film transistor is included in a pixel matrix circuit, and

wherein the pixel matrix circuit and the driver circuit are formed over an insulating surface.

79. (previously presented) A device according to claim 48, further comprising a driver circuit comprising a second thin film transistor,

wherein the first thin film transistor is included in a pixel matrix circuit, and

wherein the pixel matrix circuit and the driver circuit are formed over an insulating surface.

80. (previously presented) A device according to claim 50, further comprising a driver circuit comprising a second thin film transistor,

wherein the first thin film transistor is included in a pixel matrix circuit, and

wherein the pixel matrix circuit and the driver circuit are formed over an insulating surface.

81. (previously presented) A device according to claim 52, further comprising a driver circuit comprising a second thin film transistor,

wherein the first thin film transistor is included in a pixel matrix circuit, and

wherein the pixel matrix circuit and the driver circuit are formed over an insulating surface.

82. (previously presented) A device according to claim 54, further comprising a driver circuit comprising a second thin film transistor,

wherein the first thin film transistor is included in a pixel matrix circuit, and

wherein the pixel matrix circuit and the driver circuit are formed over an insulating surface.

83. (previously presented) A device according to claim 56, further comprising a driver circuit comprising a second thin film transistor,

wherein the first thin film transistor is included in a pixel matrix circuit, and

wherein the pixel matrix circuit and the driver circuit are formed over an insulating surface.

84. (previously presented) A device according to claim 57, further comprising a driver circuit comprising a second thin film transistor,

wherein the first thin film transistor is included in a pixel matrix circuit, and

wherein the pixel matrix circuit and the driver circuit are formed over an insulating surface.

85. (previously presented) A device according to claim 58, further comprising a driver circuit comprising a second thin film transistor,

wherein the first thin film transistor is included in a pixel matrix circuit, and

wherein the pixel matrix circuit and the driver circuit are formed over an insulating surface.

86. (previously presented) A device according to claim 59, further comprising a driver circuit comprising a second thin film transistor,

wherein the first thin film transistor is included in a pixel matrix circuit, and

wherein the pixel matrix circuit and the driver circuit are formed over an insulating surface.

87. (previously presented) A device according to claim 60, further comprising a driver circuit comprising a second thin film transistor,

wherein the first thin film transistor is included in a pixel matrix circuit, and

wherein the pixel matrix circuit and the driver circuit are formed over an insulating surface.



88. (previously presented) A device according to claim 61, further comprising a driver circuit comprising a second thin film transistor,

wherein the first thin film transistor is included in a pixel matrix circuit, and

wherein the pixel matrix circuit and the driver circuit are formed over an insulating surface.